

Ultra-Compact GaN-BDS-Based Single-Stage Isolated 1- Φ /3- Φ -Operable Bidirectional OBCs

Johann W. Kolar et al.

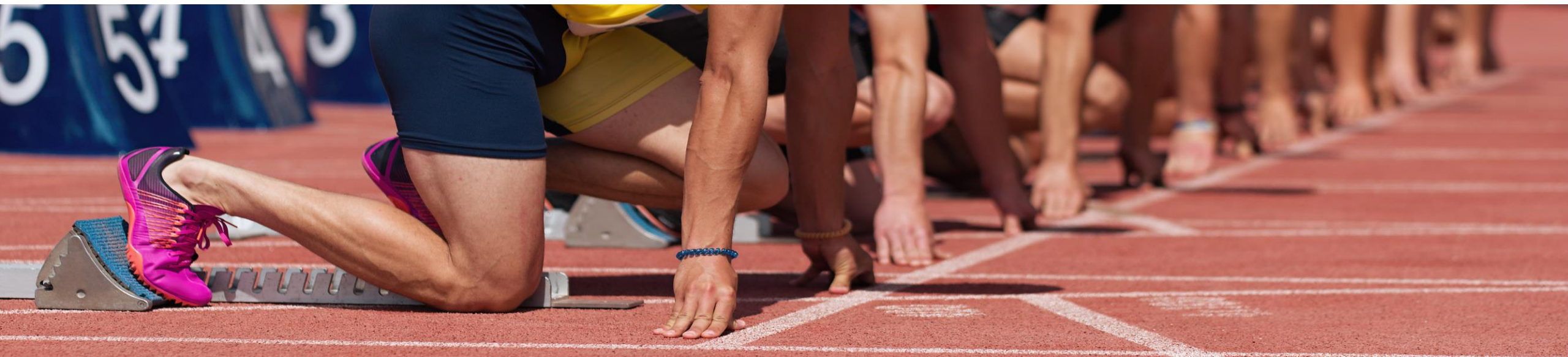


Swiss Federal Institute of Technology (ETH) Zurich
Power Electronic Systems Laboratory
www.pes.ee.ethz.ch

*Special
Session*

Bidirectional
Switches
are Coming!
Are You Ready?

Nov. 1, 2023



Ultra-Compact GaN-BDS-Based Single-Stage Isolated 1- Φ /3- Φ -Operable Bidirectional OBCs

J. W. Kolar, J. E. Huber, D. Menzi, D. Zhang, J. Schäfer, S. Weihe



Swiss Federal Institute of Technology (ETH) Zurich
Power Electronic Systems Laboratory
www.pes.ee.ethz.ch

*Special
Session*

Bidirectional
Switches
are Coming!
Are You Ready?

Nov. 1, 2023

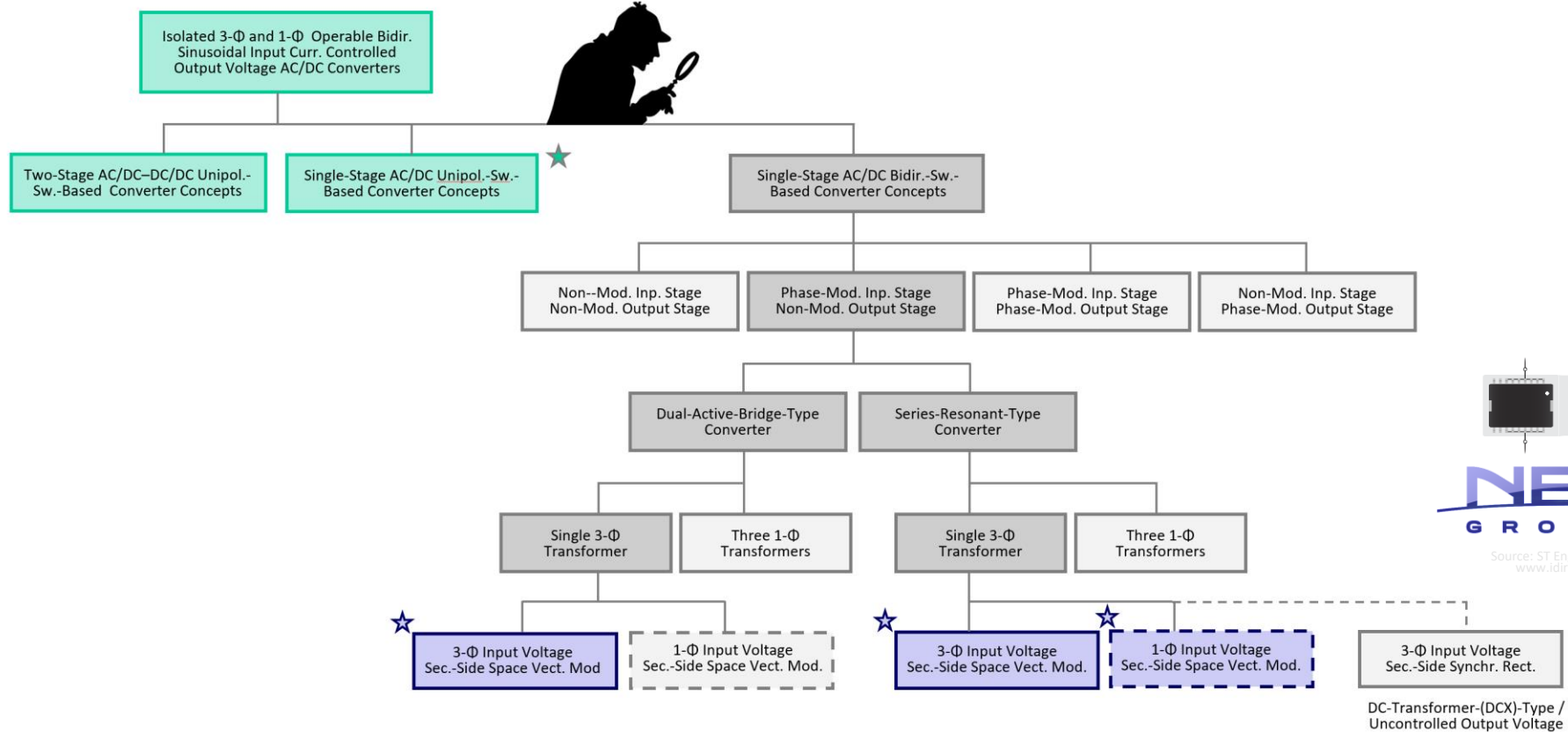


Outline



- ▶ *Introduction*
- ▶ *Non-Modular DAB-Type Matrix Converter*
- ▶ *Partly-Modular DAB-Type Converter*
- ▶ *Partly-Modular Series Res. Converter*
- ▶ *Exp. Analysis of BDS Samples*
- ▶ *Conclusions*

Classification of AC/DC-Converter Topologies



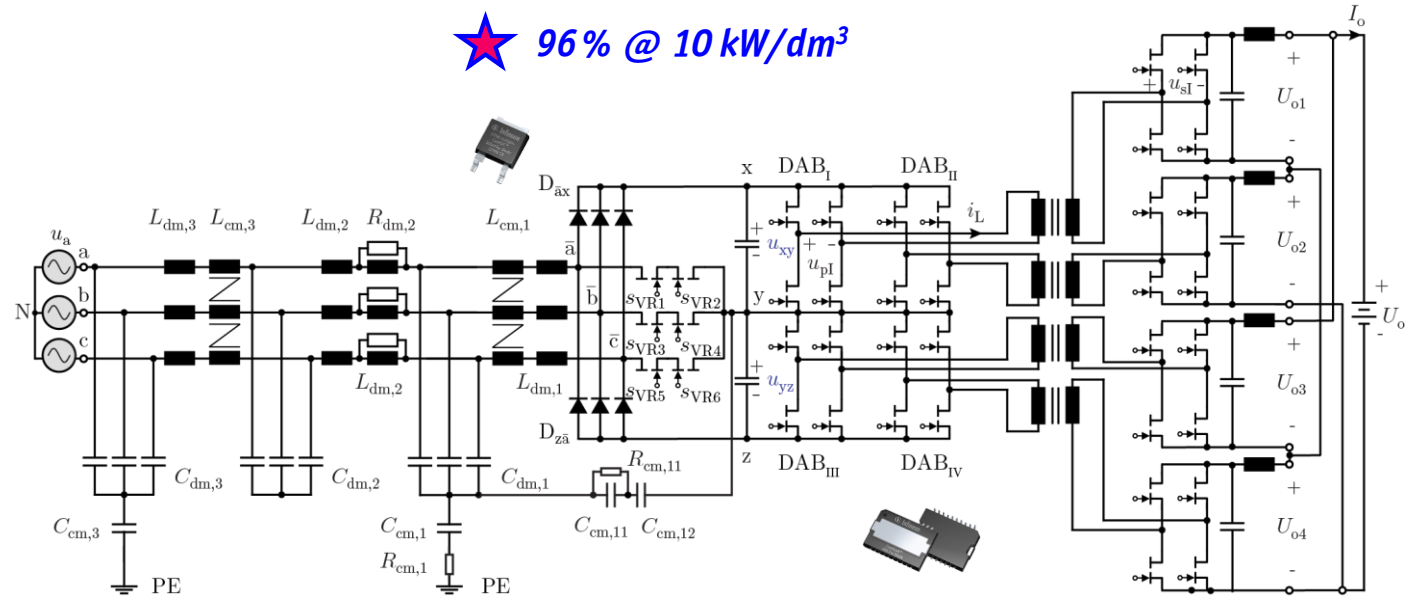
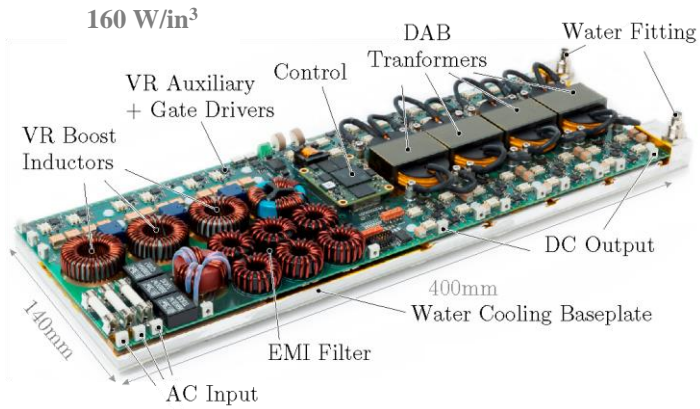
- Numerous New BDS-Based Single-Stage Conv. Concepts & Related Mod. Schemes (!)

Isolated Two-Stage 3- Φ AC/DC Converter

- 3- Φ AC/DC Converter Front-End — *Vienna Rectifier* / Split DC-Link | $f_{sw} = 560$ kHz
- 2x 2 Dual Active Bridge *DC/DC Converter* Isolation Stages | $f_{sw} = 180...330$ kHz

- $P = 10$ kW
- $U_{in} = 400$ V_{AC} line-to-line
- $U_{out} = 250 \dots 800$ V_{DC}
- CISPR 11/ Class A

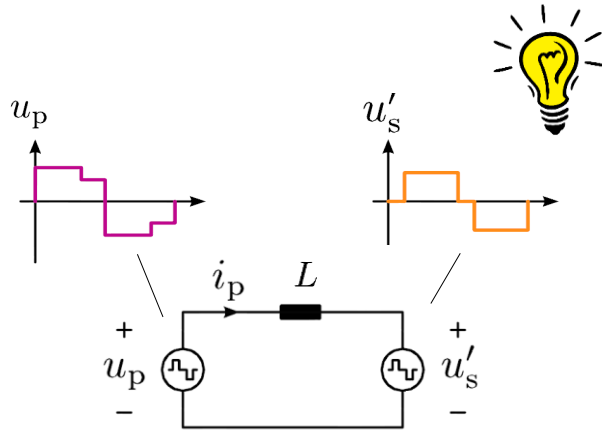
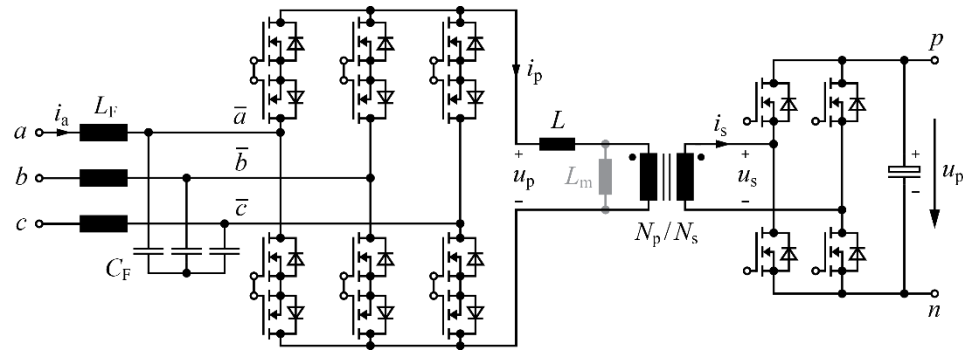
★ 96% @ 10 kW/dm³



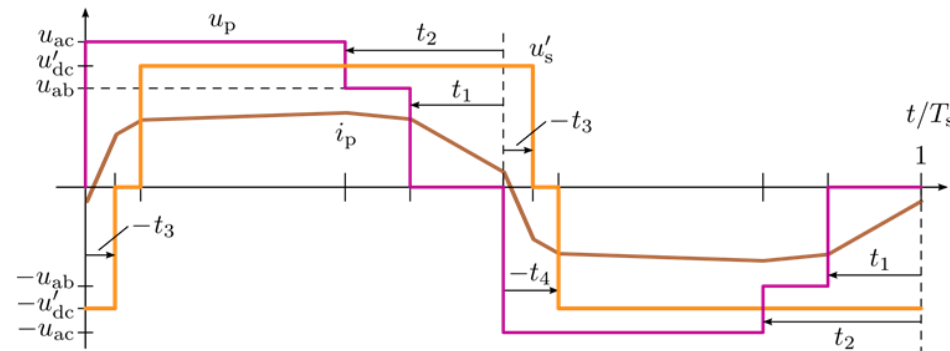
- 600V CoolGaN GIT HEMTs/ 1200V CoolSiC Schottky Diodes
- Low Sw. Loss Synergetic Control of Input & Output Stage — Six-Pulse-Shaped DC-Link Voltage

Isolated Single-Stage 3- Φ AC/DC Converter

- Low-Frequ. 3- Φ AC / High-Frequ. 1- Φ AC Matrix Converter Input Stage
- Converter Operation Based on the **Dual Active Bridge (DAB) Concept**
- **Bidirectional Buck-Boost Operation**



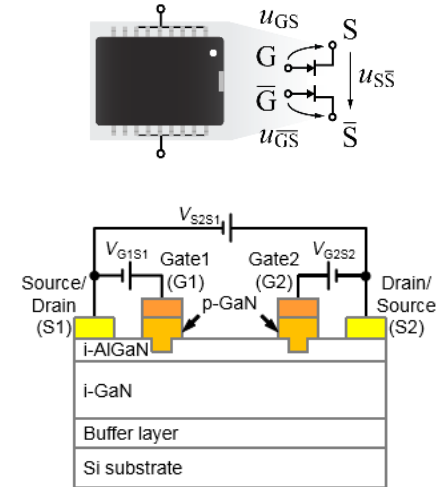
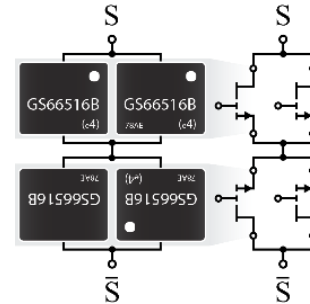
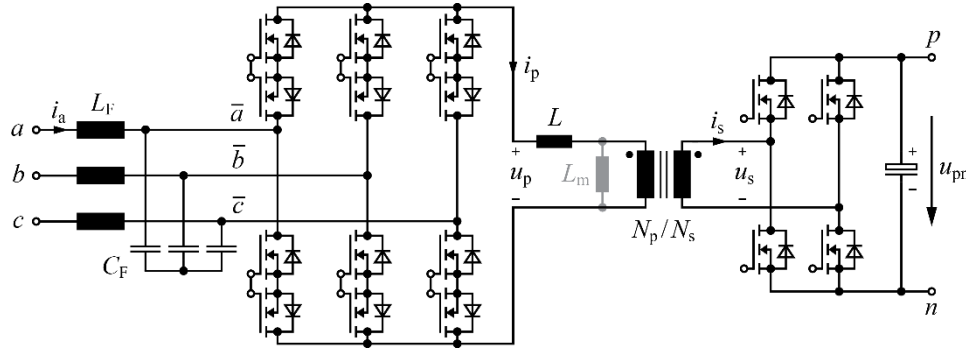
● **Equivalent Circuit**



● **Transformer Voltages / Currents**

Isolated Single-Stage 3- Φ AC/DC Converter

- Low-Frequ. 3- Φ AC / High-Frequ. 1- Φ AC Matrix Converter Input Stage
- Converter Operation Based on the **Dual Active Bridge (DAB) Concept**
- **Bidirectional Buck-Boost Operation**

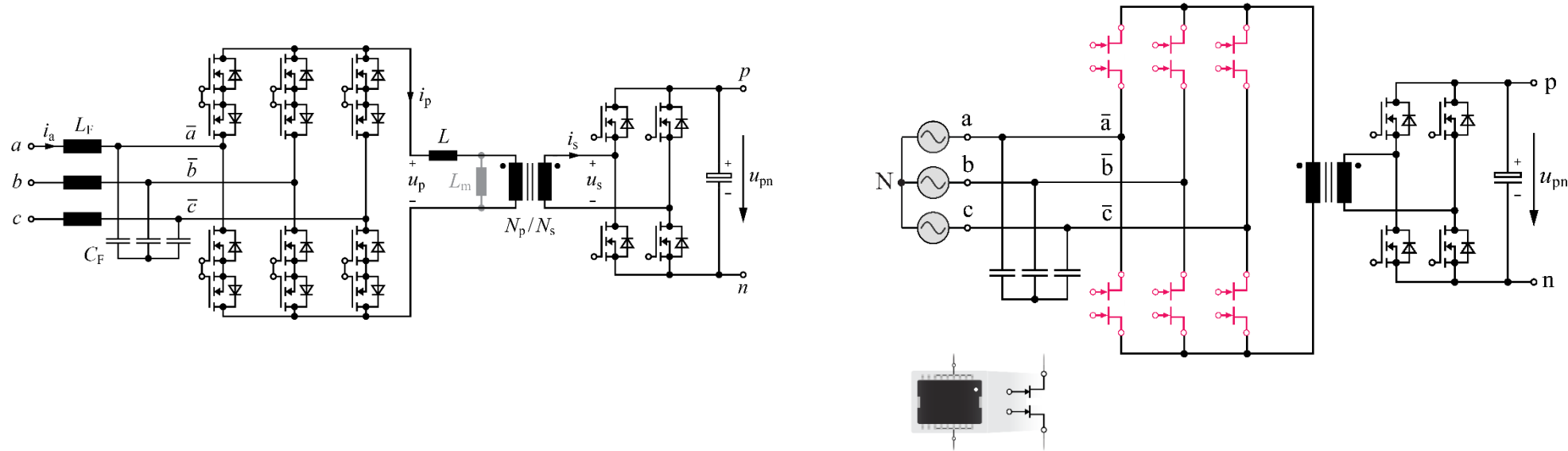


Source: **Panasonic**
ideas for life

- **Monolithic Bidirectional / Bipolar Switches (M-BDS) for Replacing Inverse-Series Conn. MOSFETs**
- **Factor of 4 Reduction of Chip Area Comp. to Discrete Realization of Same $R_{(on)}$ (!)**

Isolated Single-Stage 3- Φ AC/DC Converter

- **Monolithic Bidirectional / Bipolar Switches (M-BDS)** for Replacing Inverse-Series Conn. MOSFETs
- **Factor of 4 Reduction of Chip Area Comp. to Discrete Realization of Same $R_{(on)}$ (!)**



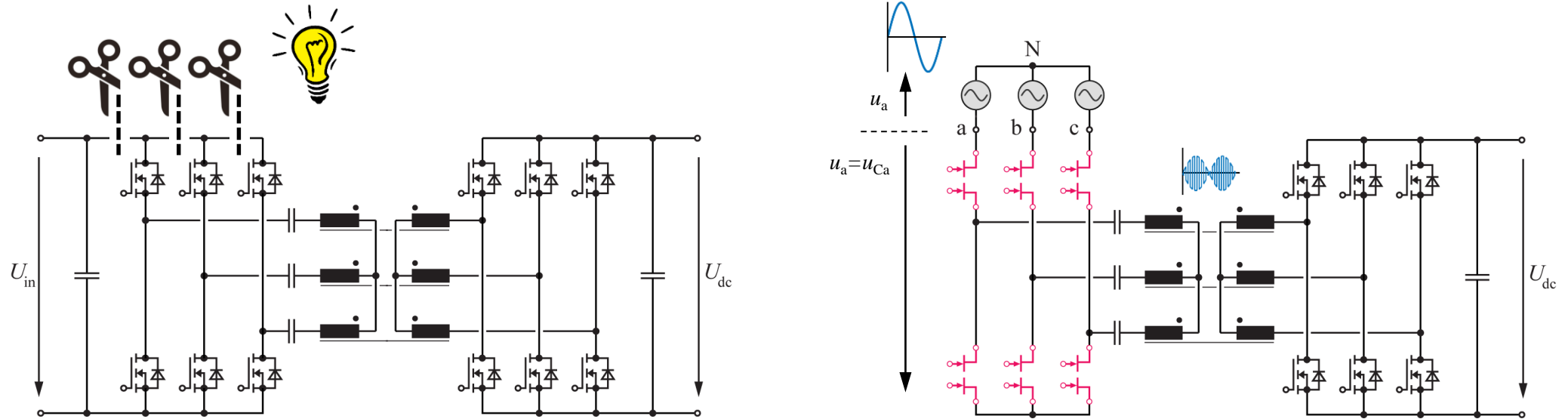
- **Rated 3- Φ Output Power NOT Available in 1- Φ Line-to-Line Operation**
- **Rated Power Operation for 3- Φ AND 1- Φ Grid Connection \rightarrow Requires Phase-Modular Input Stage**



———— *Primary-Side Phase-Modular
Converter Topology* ————

3- Φ Input DAB-Type AC/DC Converter (1)

- *Modification of 3- Φ Xfrm DAB \rightarrow Prim.-Side Phase-Modular AC/DC Converter Topology*
- *Synchronized (!) Prim.-Side Switching @ 50% Duty Cycle*

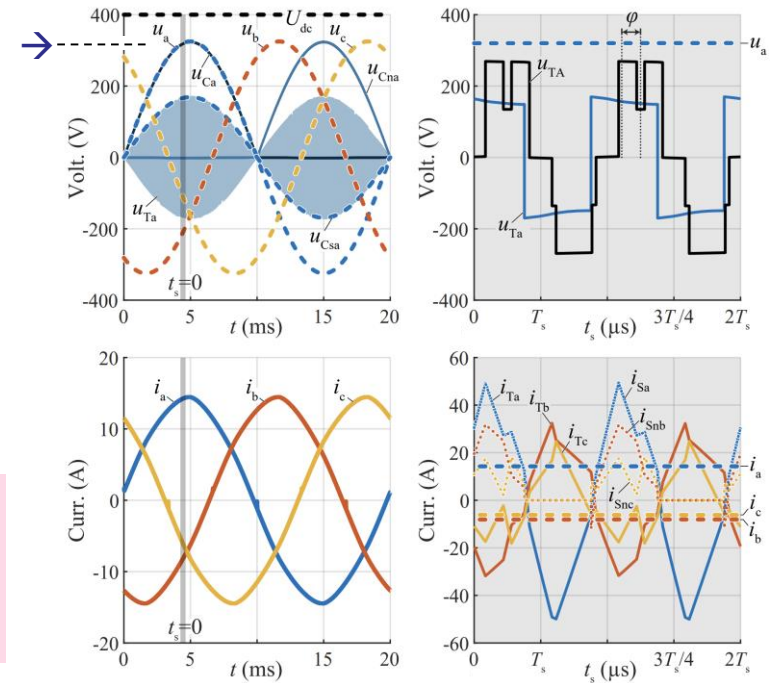
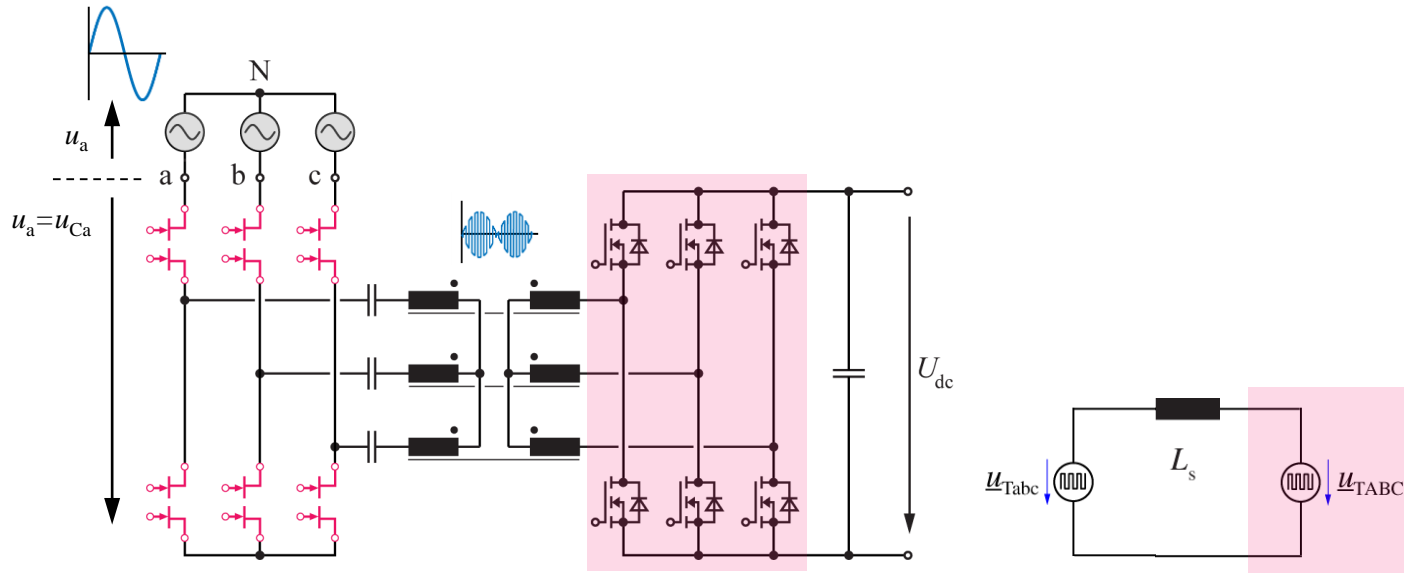


- *Voltage Stress on Prim.-Side AC Switches Determined by Peak Value of Grid PHASE Voltage (!)*
- *Bidirectional Power Flow*

3- Φ Input DAB-Type AC/DC Converter (2)

P704 | New 600V GaN Single-Stage Isolated Bidirectional 400V Input Three-Phase PFC Rectifier [#1675]
 David Menzi, Johann W. Kolar, Hector Sarnago, Oscar Lucia and Jonas E. Huber
 ETH Zurich, Switzerland; University of Zaragoza, Spain

- **Synchronized (!) Prim.-Side Switching @ 50% Duty Cycle**
- **Dual-Active-Bridge-(DAB)-Type Operation | Low-Frequ. Blocking Series Capacitors**
- **Sec.-Side Modulation Ensures Sinusoidal Input Currents & Defines Power Flow**

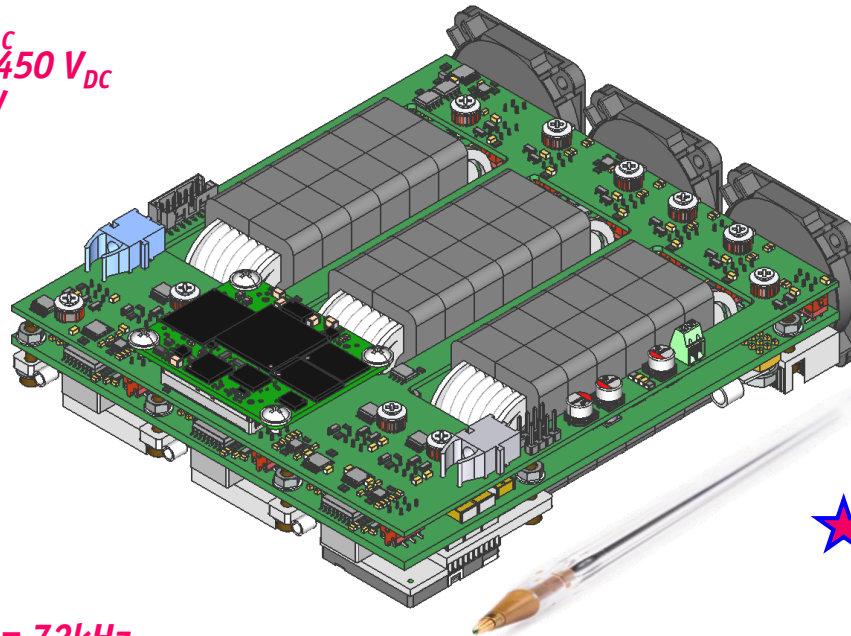


- **Allows Bidirectional Buck-Boost Operation**
- **Full Rated Power Operation @ 3- Φ AND 1- Φ Grid Input (!)**

3- Φ Input DAB-Type AC/DC Converter (3)

- **Voltage Stress on AC-Side Power Transistors Determined by PHASE Voltage Amplitude (!)**
- **600V GaN MBDS for 400V RMS Line-to-Line Grid ($U_{L-L,pk} = 560V$)**
- **Unity Power Factor / Bidirectional**

- **Line-to-Line Input** $400 V_{AC}$
- **DC Output** $250...450 V_{DC}$
- **Rated Output Power** $6.6 kW$



★ **98% (typ.) @ 8kW/dm³**

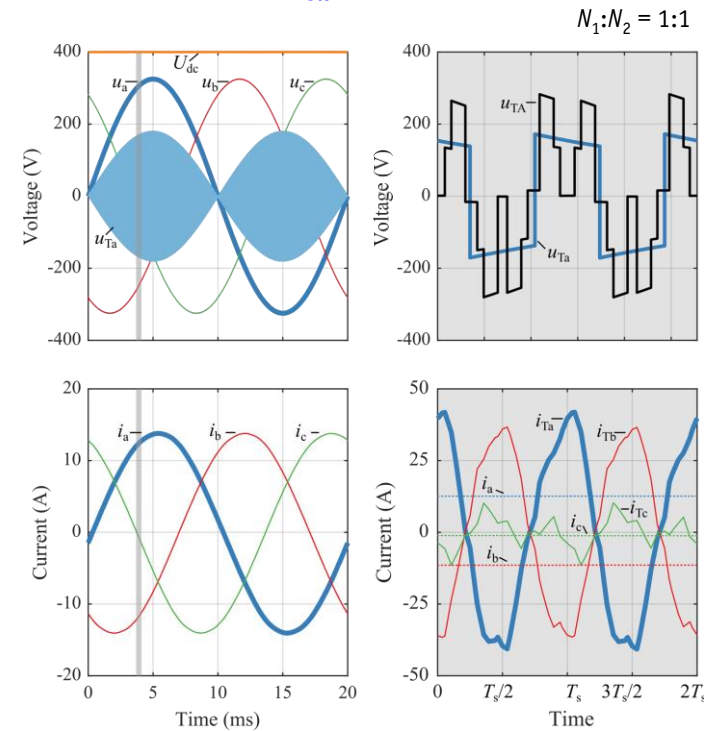
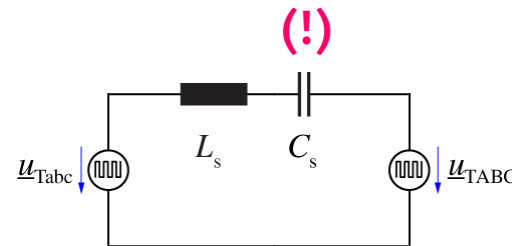
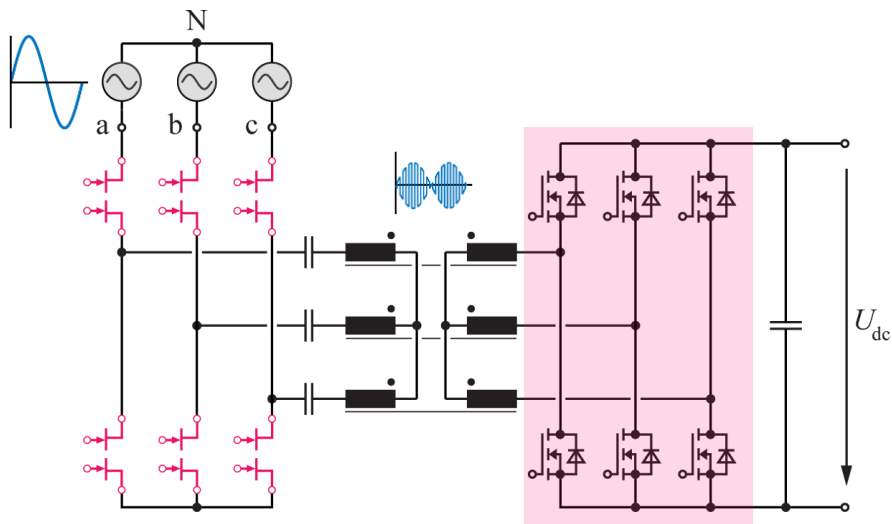
- **Prim.-Side Sw. Frequency $f_{sw} = 72kHz$**
- **$14.5 \times 13.1 \times 3.7 cm^3 / 5.7 \times 5.2 \times 1.5 in^3$**
- **Power Density w/ EMI-Filter $\approx 6kW/dm^3$ (98W/in³)**

***New 3- Φ OR 1- Φ Operable
Resonant AC/DC Converter***



3-Φ Input Resonant AC/DC Converter

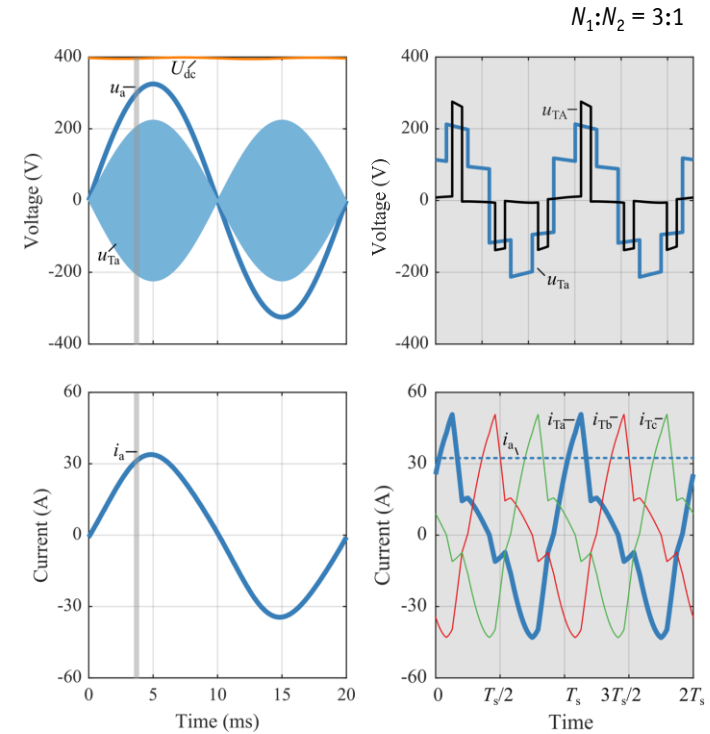
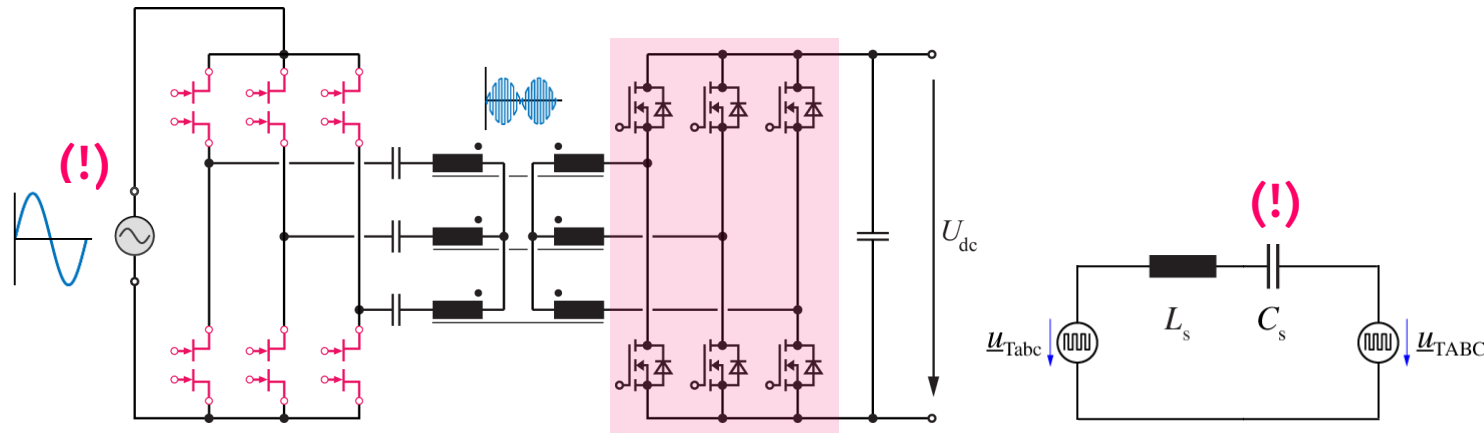
- Synchronized (!) Prim.-Side Switching @ 50% Duty Cycle | Series Res. Circuit L_{stray} , C_{res} Tuned to f_{sw}
- Sec.-Side Modulation Replicates Prim.-Side Phase Voltage Local Avg. Values / Operates @ $2 \times f_{sw}$



- Boost Operation w/ Sec.-Side Zero Volt. Intervals | Buck Operation w/ Prim.-Side Zero Volt. Intervals
- Sinusoidal Grid Currents / Bidirectional Power Flow

1- Φ Input Resonant AC/DC Converter

- All Prim.-Side Phase Modules Operated in Parallel
- 120° Phase-Shifted Sw. @ 50% Duty Cycle & Res. Frequency
- 3- Φ Sw. Freq. Six-Step Voltage Syst. Applied to Xfrm Primary
- Sec.-Side Mod. Replicates Prim.-Side Phase Voltage Local Avg. Values



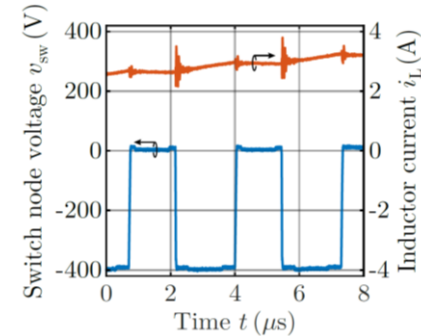
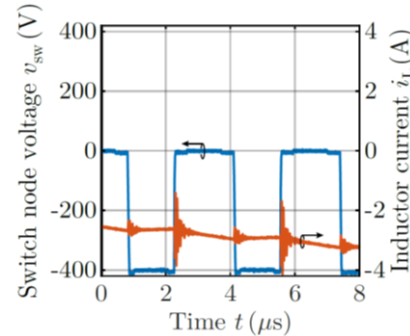
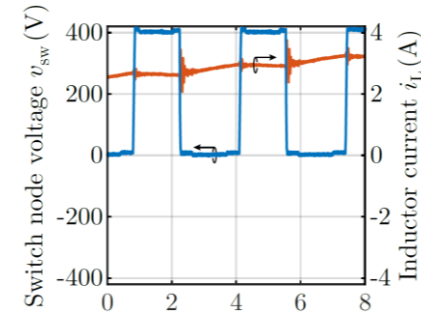
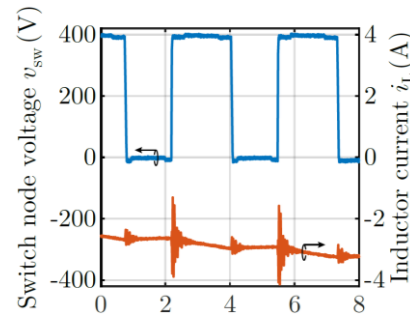
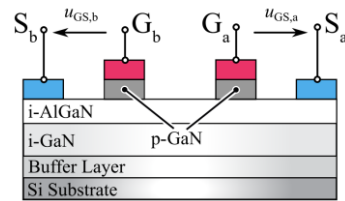
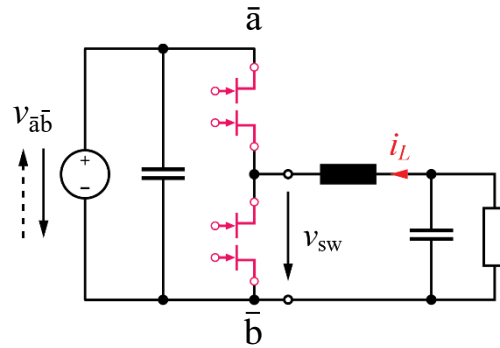
- Boost Operation w/ Sec.-Side Zero Volt. Intervals | Buck Operation w/ Prim.-Side Zero Volt. Intervals
- Sinusoidal Grid Currents / Bidirectional Power Flow



— — — — —
*Experimental
Analysis of 600V GaN
BDS-Samples*

Exp. Analysis of 1st Gen. 600V GaN M-BDS

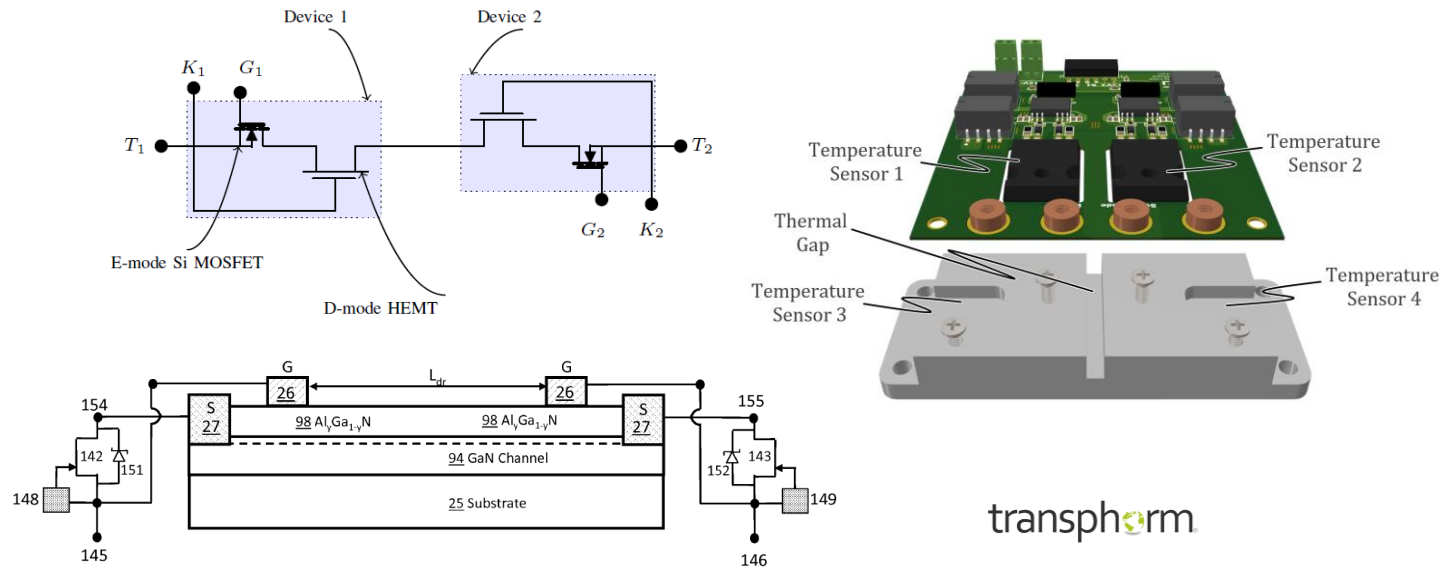
- **POWERAMERICA Program** — Based on Infineon’s CoolGaN™ HEMT Technology
- **Dual-Gate Device / Controllability of Currents in Both Directions**
- **Bipolar Voltage Blocking Capability | Normally-On or Normally-Off**



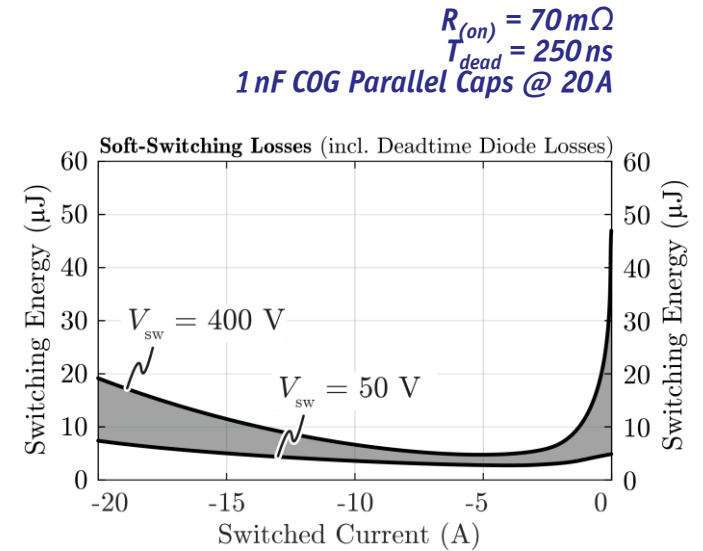
- Analysis of 4-Quadrant Operation of $R_{DS(on)} = 140m\Omega$ | 600V Sample @ $\pm 400V$
- Shared Drift Region \rightarrow “True” Monolithic Bidirectional Switch (TM-BDS)

Four-Quadrant Cascode GaN Switch (FQS)

- Common-Drain Arrangement of Two **Cascode Switches** (600V GaN D-Mode HEMT + LV Si E-Mode MOSFET)
- Up to **1200V** Samples for Demonstration Purposes



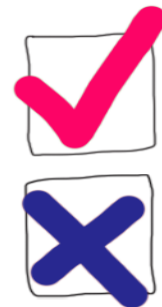
Honea et al., 2008



- 4Q** — Current Conduction Only in Quadrants I & III
- Shared Drift Region for Blocking Pos. & Neg. Voltage & Separate Cascode MOSFETs

Bi-Directional Switches are Coming !

**ARE YOU
READY?**



- **Samples Tested**
- **New Topologies Invented ?**
- **Patents Filed ?**
- **Demonstrators Built ?**